

Amend claim 16 as follows:

16. (Amended) The method of claim 1, wherein the first transistor device comprises a PMOS transistor, wherein the second transistor device comprises an NMOS transistor, and wherein implanting the first transistor region and a portion of the second transistor region [using the first implantation process] comprises implanting phosphorus in the first transistor region and a portion of the second transistor region.

Amend claim 22 as follows:

22. (Twice Amended) The method of claim 21, further comprising the steps of forming a source/drain region of the third transistor device [using a second LDD implantation process].

Amend claim 24 as follows:

24. (Twice Amended) The method of claim 18, wherein the first transistor device comprises an NMOS transistor, wherein the second transistor device comprises a PMOS transistor, and wherein adjusting a threshold voltage of the first transistor device and forming a source/drain region of the second transistor device [using the first threshold adjust implantation process] comprises selectively implanting a first transistor region associated with the first transistor device, and implanting a portion of a second transistor region associated with the second transistor device to form a source/drain region associated with the second transistor device using boron.